

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3400213	(substrate or semiconductor or wafer) nearp (active near layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 14:31
L2	38332	(substrate or semiconductor or wafer) near9 (active near layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 14:31
L3	19	(substrate or semiconductor or wafer) near9 (active near layer) and (decoupl\$4 near layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 14:32
L4	0	(germanium or "Ge") near9 (substrate or semiconductor or wafer) near9 (active near layer) and (decoupl\$4 near layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 14:33
L5	0	((germanium or "Ge") near9 (substrate or semiconductor or wafer)) near9 (active near layer) and (decoupl\$4 near layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 14:33
L6	10	((germanium or "Ge") near9 (substrate or semiconductor or wafer)) and (active near layer) and (decoupl\$4 near layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 14:33
L7	10	((germanium or "Ge") near9 (substrate or semiconductor or wafer)) and (active near layer) and (decoupl\$4 near layer) and temperature	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 14:34

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L8	4	((germanium or "Ge") near9 (substrate or semiconductor or wafer)) and (active near layer) and (decoupl\$4 near layer) and temperature and "AlGaInP"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 14:36
L9	2396	"AlGaInP" near9 (semiconductor or substrate or wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 14:37
L10	592	"AlGaInP" near9 (semiconductor or substrate or wafer) near9 (active near layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 14:37
L11	3	"AlGaInP" near9 (semiconductor or substrate or wafer) near9 (active near layer) and (decoupl\$4 near layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 14:59
L12	0	"AlGaInP" near9 (semiconductor or substrate or wafer) near9 (active near layer) and (decoupl\$4 near layer) and (438/478.ccls.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 14:59
S1	7	((("3745423") or ("4218270") or ("5233204"))).PN. or (WO02/09242).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/03/14 14:18
S2	0	S1 and (substrate or wafer or semiconductor) and "GaP" and "GaInAlP" and germanium and temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/03/14 14:23
S3	0	(germanium near4 (substrate or wafer or semiconductor)) and "GaP" and "GaInAlP" and (temperature or heat\$4 or thermal\$4) and gallium and "OMVPE"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/03/14 14:24

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S4	0	(germanium near4 (substrate or wafer or semiconductor)) and "GaP" and "GaInAlP" and (temperature or heat\$4 or thermal\$4) and gallium	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/03/14 14:25
S5	0	(germanium near4 (substrate or wafer or semiconductor)) and "GaP" and "GaInAlP" and (temperature or heat\$4 or thermal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/03/14 14:25
S6	0	(germanium near4 (substrate or wafer or semiconductor)) and "GaP" and "GaInAlP"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/03/14 14:25
S7	11	(substrate or wafer or semiconductor) and "GaP" and "GaInAlP"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/03/14 14:25
S8	9	(substrate or wafer or semiconductor) and "GaP" and "GaInAlP" and temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/03/14 14:25
S9	1	(substrate or wafer or semiconductor) and "GaP" and "GaInAlP" and temperature and butyl	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/03/14 14:26
S10	51629	(substrate or wafer or semiconductor) and "GaP" and "GaInAlP" and temperature phosphine	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/03/14 14:26
S11	1	(substrate or wafer or semiconductor) and "GaP" and "GaInAlP" and temperature and phosphine	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/03/14 14:26
S12	9	(substrate or wafer or semiconductor) and "GaP" and "GaInAlP" and temperature	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/14 14:26
S13	9	(substrate or wafer or semiconductor) and "GaP" and "GaInAlP" and temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/14 14:27

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S14	1	(substrate or wafer or semiconductor) and "GaP" and "GaInAlP" and temperature and germanium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/14 14:27
S15	9	(substrate or wafer or semiconductor) and "GaP" and "GaInAlP" and temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/14 14:29
S16	0	(germanium near4(substrate or wafer or semiconductor)) and "GaP" and "GaInAlP" and temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/14 14:29
S17	16597	(germanium near4(substrate or wafer or semiconductor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/14 14:29
S18	4115	(germanium near4(substrate or wafer or semiconductor)) and "GaP"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/14 14:29
S19	0	(germanium near4(substrate or wafer or semiconductor)) and "GaP" and "GaInAlP"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/14 14:30
S20	35	(germanium near4(substrate or wafer or semiconductor)) and "GaP" and "AlGaInP"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/14 14:31
S21	32	(germanium near4(substrate or wafer or semiconductor)) and "GaP" and "AlGaInP" and (temperature or heat or thermal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/14 14:31

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S22	0	(germanium near4(substrate or wafer or semiconductor)) and "GaP" and "AlGaInP" and (temperature or heat or thermal) and phosphie	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/14 14:32
S23	17227341	n	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/14 14:32
S24	10	(germanium near4(substrate or wafer or semiconductor)) and "GaP" and "AlGaInP" and (temperature or heat or thermal) and phosphine	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/14 14:32
S25	1	(germanium near4(substrate or wafer or semiconductor)) and "GaP" and "AlGaInP" and (temperature or heat or thermal) and (butyl near4 phosphine)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/14 14:32
S26	8	(germanium near4(substrate or wafer or semiconductor)) and "GaP" and "AlGaInP" and (temperature or heat or thermal) and phosphine and gallium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/14 14:42
S27	35	"AlGaInP" and "GaP" and (germanium near4(substrate or wafer or semiconductor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/14 14:48
S28	35	"AlGaInP" and ("GaP" or "gallium phosphide") and (germanium near4(substrate or wafer or semiconductor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/14 14:55
S29	41	"AlGaInP" and ("GaP" or (gallium near4 phosph\$4)) and (germanium near4(substrate or wafer or semiconductor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/14 14:56

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S30	21	"AlGaInP" and (gallium near4 phosph\$4) and (germanium near4(substrate or wafer or semiconductor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/14 15:03
S31	13	"AlGaInP" and "gallium phosphide" and (germanium near4(substrate or wafer or semiconductor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 08:00
S32	10	"LED" and "AlGaInP" and (gallium near4 phosph\$4) and (germanium near4 substrate) and temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 08:55
S33	19	"AlGaInP" and (gallium near4 phosph\$4) and ("TMG" or trimethylgallium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 08:56
S34	6	"AlGaInP" and (gallium near4 phosph\$4) and ("TMG" or trimethylgallium) and ("BP" or butylphosphine)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 08:57
S35	4	"AlGaInP" and (gallium near4 phosph\$4) and ("TMG" or trimethylgallium) and ("BP" or butylphosphine) and temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 09:00
S36	0	"AlGaInP" and ("TMG" or trimethylgallium) and ("BP" or butylphosphine) and temperature and "OMVPE"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 09:01
S37	624	"OMVPE"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 09:01

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S38	68	"OMVPE" and "AlGaInP"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 09:02
S39	60	"OMVPE" and "AlGaInP" and temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 09:02
S40	0	"OMVPE" and "AlGaInP" and temperature and ("BP" or butylphosphine)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 09:02
S41	0	"OMVPE" and "AlGaInP" and temperature and butylphosphine	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 09:02
S42	4	"OMVPE" and "AlGaInP" and temperature and trimethylgallium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 09:03